



500.37328X00

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): YOKOGAWA, et al  
Serial No.: 09/336,687  
Filed: June 21, 1999  
For: PLASMA PROCESSING SYSTEM AND METHOD  
Group: 1763  
Examiner: L. Alejandro

#6A  
6/18/01  
RECEIVED  
TECHNOLOGY CENTER 1700

AMENDMENT

Commissioner for Patents  
Washington, D.C. 20231

June 4, 2001

Sir:

The following amendments and remarks are respectfully submitted in connection with the above-identified application in response to the Office Action dated January 3, 2001.

IN THE SPECIFICATION:

Page 1, replace the paragraph beginning at line 6 and bridging pages 1 and 2 with the following new paragraph:

A1  
A plasma processing system conventionally employed to fabricate semiconductor devices, for example, a plasma etching system has been described in pages 55 to 58 of "Hitachi Hyouron", Vol. 76, No. 7 published in 1994. This is a magneto-microwave plasma etching system in which electromagnetic waves in a microwave range are introduced via